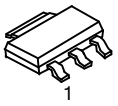
PZT1816

NPN PLANAR TRANSISTOR

HIGH CURRENT SWITCHIG APPLICATIONS



SOT-223

■ FEATURES

* Low collector-to-emitter saturation voltage
* Good linearity of h_{FE}
* Small and slim package facilitating compactness of sets.
* High f_T
* Fast switching speed

■ ORDERING INFORMATION

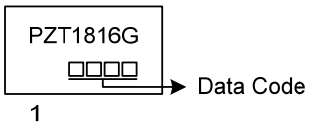
Ordering Number	Package	Pin Assignment			Packing
		1	2	3	
PZT1816G-x-AA3-R	SOT-223	B	C	E	Tape Reel

PZT1816G-x-AA3-R

(1)Packing Type
(2)Packing Type
(3)Rank
(4)Green Package

(1) R: Tape Reel
(2) AA3: SOT-223
(3) x: refer to Classification of h_{FE1}
(4) G: Halogen Free and Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	120	V
Collector-Emitter Voltage		V_{CEO}	100	V
Emitter-Base Voltage		V_{EBO}	6	V
Collector Current	DC	I_C	4	A
	PULSE(Note 2)		8	A
Power Dissipation		P_D	1	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-40 ~ +150	°C

Note1: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2: Duty=1/2, Pw=20ms

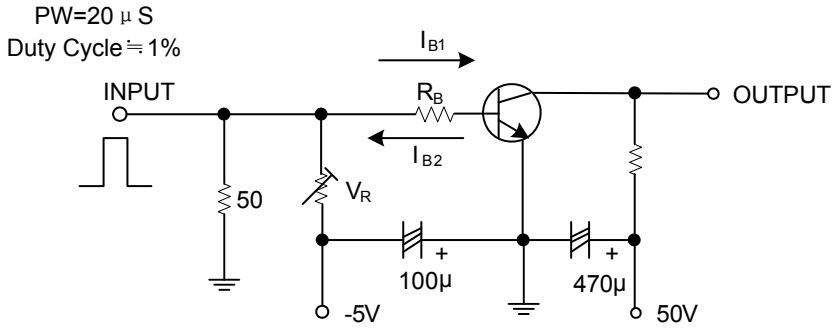
■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Base Breakdown Voltage	BV_{CBO}	I_C =10μA, I_E =0	120			V
Collector Emitter Breakdown Voltage	BV_{CEO}	I_C =1mA, R_B=∞	100			V
Emitter Base Breakdown Voltage	BV_{EBO}	I_E =10μA, I_C=0	6			V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	I_C = 2A, I_B =0.2A		0.9	1.2	V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I_C = 2A, I_B=0.2A		150	400	mV
Collector Cut-Off Current	I_{CBO}	V_{CB} = 100 V, I_E =0			1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB} = 4V, I_C=0			1	μA
DC Current Transfer Ratio	h_{FE1}	V_{CE} = 5V, I_C = 0.5A	70		400	
	h_{FE2}	V_{CE} =5V, I_C = 3A	40			
Transition Frequency	f_T	V_{CE} =10V, I_C =0.5A		180		MHz
Output Capacitance	C_{ob}	V_{CB} =10V, I_E =0A, f =1MHz		40		pF
Turn-on Time	t_{ON}	See test circuit		100		ns
Storage Time	t_{STG}	See test circuit		900		ns
Fall Time	t_F	See test circuit		50		ns

■ CLASSIFICATION of h_{FE1}

RANK	R	S	T	Q
RANGE	100 - 200	140 - 280	200 - 400	70 -140

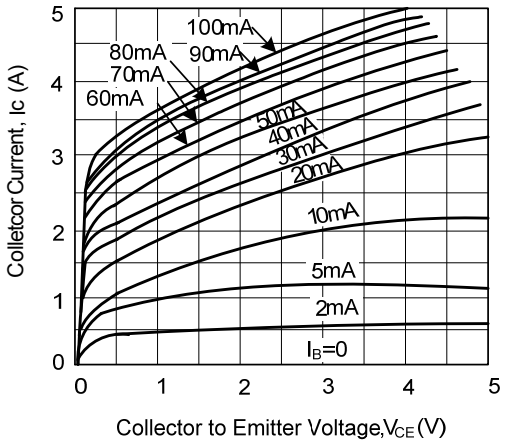
■ TEST CIRCUIT



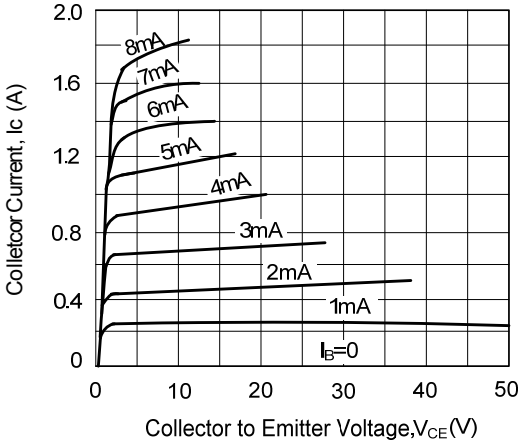
Ic=10, I_{B1}= -10, I_{B2}=2A
Unit (resistance: Ω , capacitance: F)

■ TYPICAL CHARACTERISTICS

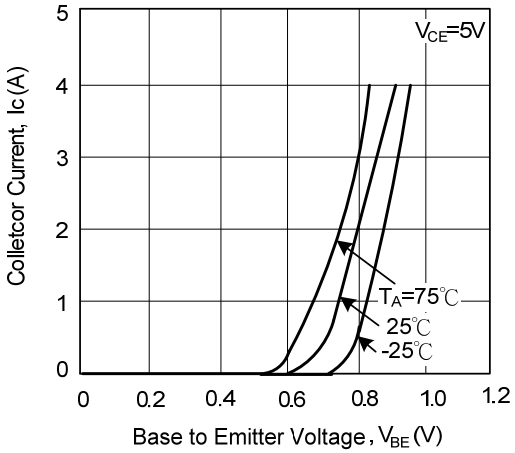
Ic-V_{CE}



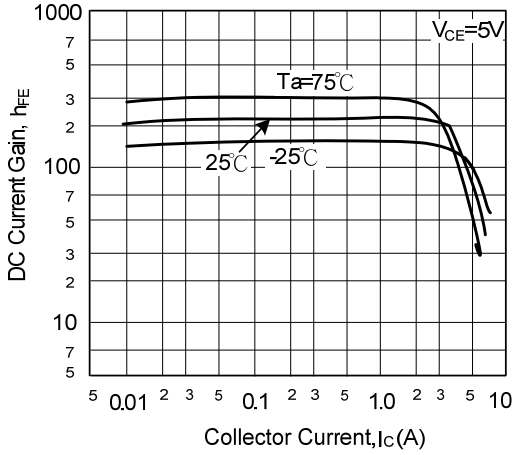
Ic-V_{CE}



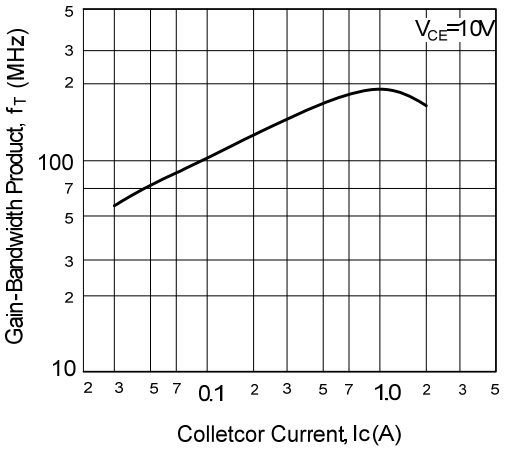
Ic-V_{BE}



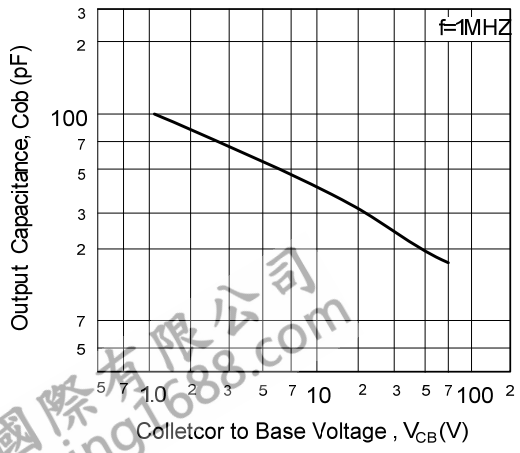
h_{FE}-Ic



f_T-I c



Cob-V_{CB}



■ TYPICAL CHARACTERISTICS(Cont.)